Features

- Serial Peripheral Interface (SPI) Compatible
- Supports SPI Modes 0 (0,0) and 3 (1,1) - Datasheet Describes Mode 0 Operation
- Low-voltage and Standard-voltage Operation
- -1.8 (V_{cc} = 1.8V to 5.5V)
- 20 MHz Clock Rate (5V)
- 32-byte Page Mode
- Block Write Protection
 - Protect 1/4, 1/2, or Entire Array
- Write Protect (WP) Pin and Write Disable Instructions for Both Hardware and Software **Data Protection**
- Self-timed Write Cycle (5 ms max)
- High Reliability
 - Endurance: One Million Write Cycles
 - Data Retention: 100 Years
- Automotive Devices Available
- 8-lead JEDEC PDIP, 8-lead JEDEC SOIC, 8-lead Ultra Thin Mini-MAP (MLP 2x3), 8-lead TSSOP and 8-lead Ultra Lead Frame Land Grid Array (ULA) Packages
- · Die Sales: Wafer Form, Tape and Reel, and Bumped Wafers

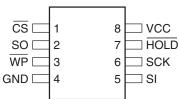
Description

The AT25320B/640B provides 32768/65536 bits of serial electrically-erasable programmable read-only memory (EEPROM) organized as 4096/8192 words of 8 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The AT25320B/640B is available in space-saving 8-lead PDIP, 8-lead JEDEC SOIC, 8-lead Ultra Thin Mini-MAP (MLP 2x3), 8-lead Ultra Lead Frame Land Grid Array (ULA) and 8-lead TSSOP packages.

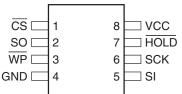
The AT25320B/640B is enabled through the Chip Select pin (\overline{CS}) and accessed via a three-wire interface consisting of Serial Data Input (SI), Serial Data Output (SO), and Serial Clock (SCK). All programming cycles are completely self-timed, and no separate erase cycle is required before write.

Table 0-1.	Pin Configuration		
Pin Name	F	Function	
CS	(Chip Select	
SCK	5	Serial Data Clock	
SI	9	Serial Data Input	
SO	5	Serial Data Output	
GND	(Ground	
VCC	F	Power Supply	
WP	١	Vrite Protect	
HOLD	5	Suspends Serial Input	

8-lead PDIP



8-lead TSSOP







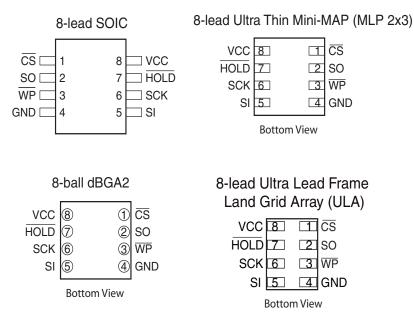
SPI Serial **EEPROMs** 32K (4096 x 8) 64K (8192 x 8)

AT25320B AT25640B

Advance Information

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Block write protection is enabled by programming the status register with one of four blocks of write protection. Separate program enable and program disable instructions are provided for additional data protection. Hardware data protection is provided via the WP pin to protect against inadvertent write attempts to the status register. The HOLD pin may be used to suspend any serial communication without resetting the serial sequence.

Absolute Maximum Ratings*

Operating Temperature55°C to +125°C
Storage Temperature65°C to +150°C
Voltage on Any Pin with Respect to Ground1.0V to +7.0V
Maximum Operating Voltage 6.25V
DC Output Current 5.0 mA

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

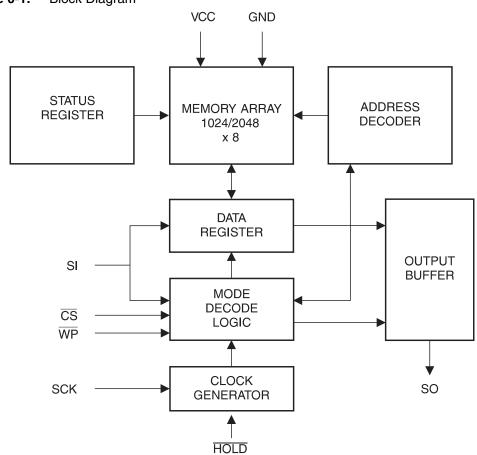


Figure 0-1. Block Diagram

Table 0-2.Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25^{\circ}C$, f = 1.0 MHz, $V_{CC} = +5.0V$ (unless otherwise noted)

Symbol	Test Conditions	Max	Units	Conditions
C _{OUT}	Output Capacitance (SO)	8	pF	$V_{OUT} = 0V$
C _{IN}	Input Capacitance (CS, SCK, SI, WP, HOLD)	6	pF	$V_{IN} = 0V$

Note: 1. This parameter is characterized and is not 100% tested.





Table 0-3. DC Characteristics

Symbol	Parameter	Test Condition		Min	Тур	Мах	Units
V _{CC1}	Supply Voltage		1.8		5.5	V	
V _{CC2}	Supply Voltage			2.7		5.5	V
V _{CC3}	Supply Voltage			4.5		5.5	V
I _{CC1}	Supply Current	V _{CC} = 5.0V at 20 MHz, 5	SO = Open, Read		7.5	10.0	mA
I _{CC2}	Supply Current	V _{CC} = 5.0V at 20 MHz, S Write	O = Open, Read,		4.0	10.0	mA
I _{CC3}	Supply Current	V _{CC} = 5.0V at 5 MHz, S Read, Write		4.0	6.0	mA	
I _{SB1}	Standby Current	$V_{CC} = 1.8V, \overline{CS} = V_{CC}$		< 0.1	6.0 ⁽²⁾	μA	
I _{SB2}	Standby Current	$V_{CC} = 2.7 V, \overline{CS} = V_{CC}$	$V_{CC} = 2.7V, \overline{CS} = V_{CC}$			7.0 ⁽²⁾	μA
I _{SB3}	Standby Current	$V_{CC} = 5.0V, \overline{CS} = V_{CC}$	$V_{CC} = 5.0V, \overline{CS} = V_{CC}$			10.0 ⁽²⁾	μA
I _{IL}	Input Leakage	$V_{IN} = 0V$ to V_{CC}		-3.0		3.0	μA
I _{OL}	Output Leakage	$V_{IN} = 0V$ to V_{CC} , $T_{AC} = 0$	°C to 70°C	-3.0		3.0	μA
V _{IL} ⁽¹⁾	Input Low-voltage			-0.6		V _{CC} x 0.3	V
V _{IH} ⁽¹⁾	Input High-voltage					V _{CC} + 0.5	V
V _{OL1}	Output Low-voltage		I _{OL} = 3.0 mA			0.4	V
V _{OH1}	Output High-voltage	$4.5V \le V_{CC} \le 5.5V$	I _{OH} = -1.6 mA	V _{CC} - 0.8			V
V _{OL2}	Output Low-voltage		I _{OL} = 0.15 mA			0.2	V
V _{OH2}	Output High-voltage	$1.8V \le V_{CC} \le 3.6V$	I _{OH} = -100 μA	V _{CC} - 0.2			V

Applicable over recommended operating range from: $T_{AI} = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = +1.8V$ to +5.5V (unless otherwise noted)

Notes: 1. V_{IL} min and V_{IH} max are reference only and are not tested.

2. Worst case measured at 85°C

AT25320B/640B

Table 0-4.AC Characteristics

Applicable over recommended operating range from $T_{AI} = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = As$ Specified, CL = 1 TTL Gate and 30 pF (unless otherwise noted)

Symbol	Parameter	Voltage	Min	Max	Units
f _{scк}	SCK Clock Frequency	4.5–5.5 2.7–5.5 1.8–5.5	0 0 0	20 10 5	MHz
t _{RI}	Input Rise Time	4.5–5.5 2.7–5.5 1.8–5.5		2 2 2	μs
t _{FI}	Input Fall Time	4.5–5.5 2.7–5.5 1.8–5.5		2 2 2	μs
t _{wH}	SCK High Time	4.5–5.5 2.7–5.5 1.8–5.5	20 40 80		ns
t _{wL}	SCK Low Time	4.5–5.5 2.7–5.5 1.8–5.5	20 40 80		ns
cs	CS High Time	4.5–5.5 2.7–5.5 1.8–5.5	25 50 100		ns
css	CS Setup Time	4.5–5.5 2.7–5.5 1.8–5.5	25 50 100		ns
t _{сsн}	CS Hold Time	4.5–5.5 2.7–5.5 1.8–5.5	25 50 100		ns
t _{su}	Data In Setup Time	4.5–5.5 2.7–5.5 1.8–5.5	5 10 20		ns
t _H	Data In Hold Time	4.5–5.5 2.7–5.5 1.8–5.5	5 10 20		ns
t _{HD}	HOLD Setup Time	4.5–5.5 2.7–5.5 1.8–5.5	5 10 20		
t _{cD}	HOLD Hold Time	4.5–5.5 2.7–5.5 1.8–5.5	5 10 20		ns
t _v	Output Valid	4.5–5.5 2.7–5.5 1.8–5.5	0 0 0	20 40 80	ns
t _{HO}	Output Hold Time	4.5–5.5 2.7–5.5 1.8–5.5	0 0 0		ns





 Table 0-4.
 AC Characteristics (Continued)

Applicable over recommended operating range from $T_{AI} = -40^{\circ}C$ to +85°C, V_{CC} = As Specified,

CL = 1 TTL Gate and 30 pF (unless otherwise noted)

Symbol	Parameter	Voltage	Min	Max	Units
t _{LZ}	HOLD to Output Low Z	4.5–5.5 2.7–5.5 1.8–5.5	0 0 0	25 50 100	ns
t _{HZ}	HOLD to Output High Z	4.5–5.5 2.7–5.5 1.8–5.5		40 80 200	ns
t _{DIS}	Output Disable Time	4.5–5.5 2.7–5.5 1.8–5.5		40 80 200	ns
t _{WC}	Write Cycle Time	4.5–5.5 2.7–5.5 1.8–5.5		5 5 5	ms
Endurance ⁽¹⁾	3.3V, 25°C, Page Mode		1M		Write Cycles

Note: 1. This parameter is characterized and is not 100% tested.

1. Serial Interface Description

MASTER: The device that generates the serial clock.

SLAVE: Because the Serial Clock pin (SCK) is always an input, the AT25320B/640B always operates as a slave.

TRANSMITTER/RECEIVER: The AT25320B/640B has separate pins designated for data transmission (SO) and reception (SI).

MSB: The Most Significant Bit (MSB) is the first bit transmitted and received.

SERIAL OP-CODE: After the device is selected with \overline{CS} going low, the first byte will be received. This byte contains the op-code that defines the operations to be performed.

INVALID OP-CODE: If an invalid op-code is received, no data will be shifted into the AT25320B/640B, and the serial output pin (SO) will remain in a high impedance state until the falling edge of \overline{CS} is detected again. This will reinitialize the serial communication.

CHIP SELECT: The AT25320B/640B is selected when the \overline{CS} pin is low. When the device is not selected, data will not be accepted via the SI pin, and the serial output pin (SO) will remain in a high impedance state.

HOLD: The HOLD pin is used in conjunction with the \overline{CS} pin to select the AT25320B/640B. When the device is selected and a serial sequence is underway, HOLD can be used to pause the serial communication with the master device without resetting the serial sequence. To pause, the HOLD pin must be brought low while the SCK pin is low. To resume serial communication, the HOLD pin is brought high while the SCK pin is low (SCK may still toggle during HOLD). Inputs to the SI pin will be ignored while the SO pin is in the high impedance state.

WRITE PROTECT: The write protect pin (\overline{WP}) will allow normal read/write operations when held high. When the WP pin is brought low and WPEN bit is "1", all write operations to the status register are inhibited. \overline{WP} going low while \overline{CS} is still low will interrupt a write to the status register. If the internal write cycle has already been initiated, \overline{WP} going low will have no effect on any write

operation to the status register. The \overline{WP} pin function is blocked when the WPEN bit in the status register is "0". This will allow the user to install the AT25320B/640B in a system with the \overline{WP} pin tied to ground and still be able to write to the status register. All \overline{WP} pin functions are enabled when the WPEN bit is set to "1".

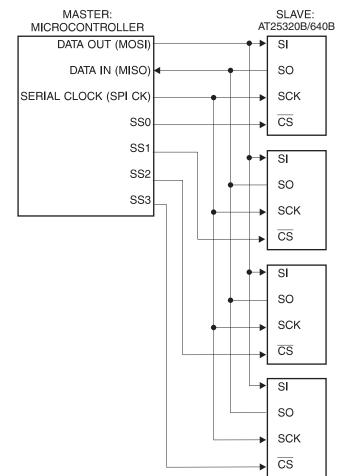


Figure 1-1. SPI Serial Interface

2. Functional Description

The AT25320B/640B is designed to interface directly with the synchronous serial peripheral interface (SPI) of the 6805 and 68HC11 series of microcontrollers.

The AT25320B/640B utilizes an 8-bit instruction register. The list of instructions and their operation codes are contained in Table 2-1. All instructions, addresses, and data are transferred with the MSB first and start with a high-to-low CS transition.

Instruction Name	Instruction Format	Operation
WREN	0000 X110	Set Write Enable Latch
WRDI	0000 X100	Reset Write Enable Latch
RDSR	0000 X101	Read Status Register

 Table 2-1.
 Instruction Set for the AT25320B/640B





Instruction Name	Instruction Format	Operation
WRSR	0000 X001	Write Status Register
READ	0000 X011	Read Data from Memory Array
WRITE	0000 X010	Write Data to Memory Array

Table 2-1.Instruction Set for the AT25320B/640B

WRITE ENABLE (WREN): The device will power up in the write disable state when V_{CC} is applied. All programming instructions must therefore be preceded by a Write Enable instruction.

WRITE DISABLE (WRDI): To protect the device against inadvertent writes, the Write Disable instruction disables all programming modes. The WRDI instruction is independent of the status of the WP pin.

READ STATUS REGISTER (RDSR): The Read Status Register instruction provides access to the status register. The READY/BUSY and Write Enable status of the device can be determined by the RDSR instruction. Similarly, the Block Write Protection Bits indicate the extent of protection employed. These bits are set by using the WRSR instruction.

Table 2-2.Status Register Format

		0					
Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
WPEN	Х	Х	Х	BP1	BP0	WEN	RDY

 Table 2-3.
 Read Status Register Bit Definition

Bit	Definition
Bit 0 (RDY)	Bit $0 = "0"$ (RDY) indicates the device is READY. Bit $0 = "1"$ indicates the write cycle is in progress.
Bit 1 (WEN)	Bit 1= "0" indicates the device is not WRITE ENABLED. Bit 1 = "1" indicates the device is write enabled.
Bit 2 (BP0)	See Table 2-4 on page 9.
Bit 3 (BP1)	See Table 2-4 on page 9.
Bits 4–6 are "0"s v	vhen device is not in an internal write cycle.
Bit 7 (WPEN)	See Table 2-5 on page 9.
Bits 0–7 are "1"s c	luring an internal write cycle.

WRITE STATUS REGISTER (WRSR): The WRSR instruction allows the user to select one of four levels of protection. The AT25320B/640B is divided into four array segments. One-quarter, one-half, or all of the memory segments can be protected. Any of the data within any selected segment will therefore be read only. The block write protection levels and corresponding status register control bits are shown in Table 2-4 on page 9.

The three bits BP0, BP1, and WPEN are nonvolatile cells that have the same properties and functions as the regular memory cells (e.g., WREN, t_{WC}, RDSR).

	Status Re	gister Bits Array Addresses Protected		ses Protected
Level	BP1	BP0	AT25320B	AT25640B
0	0	0	None	None
1(1/4)	0	1	0C00-0FFF	1800–1FFF
2(1/2)	1	0	0800-0FFF	1000–1FFF
3(All)	1	1	0000-0FFF	0000–1FFF

 Table 2-4.
 Block Write Protect Bits

The WRSR instruction also allows the user to enable or disable the write protect (\overline{WP}) pin through the use of the Write Protect Enable (WPEN) bit. Hardware write protection is enabled when the \overline{WP} pin is low and the WPEN bit is "1". Hardware write protection is disabled when either the \overline{WP} pin is high or the WPEN bit is "0". When the device is hardware write protected, writes to the status register, including the block protect bits and the WPEN bit, and the block-protected sections in the memory array are disabled. Writes are only allowed to sections of the memory that are not block-protected.

NOTE: When the WPEN bit is hardware write protected, it cannot be changed back to "0" as long as the \overline{WP} pin is held low.

WPEN	WP	WEN	Protected Unprotected Blocks Blocks		Status Register
0	Х	0	Protected	Protected	Protected
0	Х	1	Protected	Writeable	Writeable
1	Low	0	Protected	Protected	Protected
1	Low	1	Protected	Writeable	Protected
Х	High	0	Protected	Protected	Protected
Х	High	1	Protected	Writeable	Writeable

Table 2-5.WPEN Operation

READ SEQUENCE (READ): Reading the AT25320B/640B via the Serial Output (SO) pin requires the following sequence. After the \overline{CS} line is pulled low to select a device, the read opcode is transmitted via the SI line followed by the byte address to be read (A15–A0, see Table 2-6). Upon completion, any data on the SI line will be ignored. The data (D7–D0) at the specified address is then shifted out onto the SO line. If only one byte is to be read, the \overline{CS} line should be driven high after the data comes out. The read sequence can be continued since the byte address is automatically incremented and data will continue to be shifted out. When the highest address is reached, the address counter will roll over to the lowest address allowing the entire memory to be read in one continuous read cycle.

WRITE SEQUENCE (WRITE): In order to program the AT25320B/640B, two separate instructions must be executed. First, the device *must be write enabled* via the WREN instruction. Then a write (WRITE) instruction may be executed. Also, the address of the memory location(s) to be programmed must be outside the protected address field location selected by the block write protection level. During an internal write cycle, all commands will be ignored except the RDSR instruction.





A write instruction requires the following sequence. After the \overline{CS} line is pulled low to select the device, the WRITE op-code is transmitted via the SI line followed by the byte address (A15–A0) and the data (D7–D0) to be programmed (see Table 2-6). Programming will start after the \overline{CS} pin is brought high. The low-to-high transition of the \overline{CS} pin must occur during the SCK low-time immediately after clocking in the D0 (LSB) data bit.

The READY/BUSY status of the device can be determined by initiating a read status register (RDSR) instruction. If Bit 0 = "1", the write cycle is still in progress. If Bit 0 = "0", the write cycle has ended. Only the RDSR instruction is enabled during the write programming cycle.

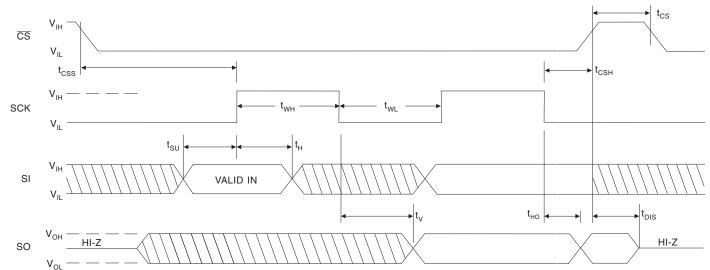
The AT25320B/640B is capable of a 32-byte page write operation. After each byte of data is received, the five low-order address bits are internally incremented by one; the high-order bits of the address will remain constant. If more than 32 bytes of data are transmitted, the address counter will roll over and the previously written data will be overwritten. The AT25320B/640B is automatically returned to the write disable state at the completion of a write cycle.

NOTE: If the device is not write-enabled (WREN), the device will ignore the write instruction and will return to the standby state, when \overline{CS} is brought high. A new \overline{CS} falling edge is required to reinitiate the serial communication.

Address	AT25320B	AT25640B
A _N	A ₁₁ -A ₀	A ₁₂ -A ₀
Don't Care Bits	A ₁₅ -A ₁₂	A ₁₅ –A ₁₃

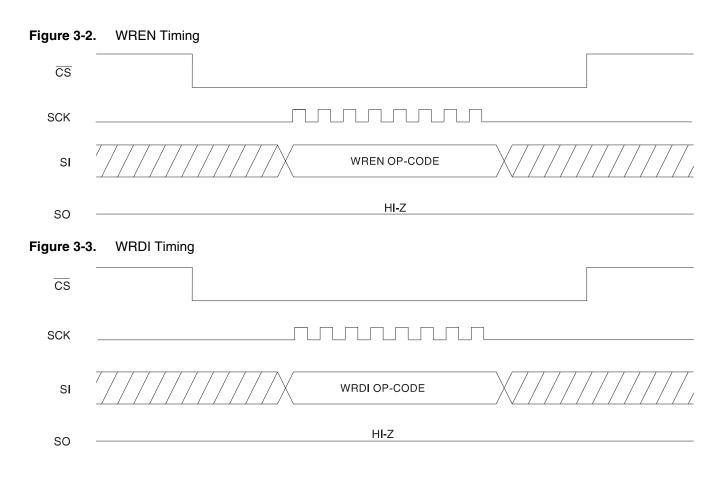
3. Timing Diagrams

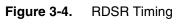


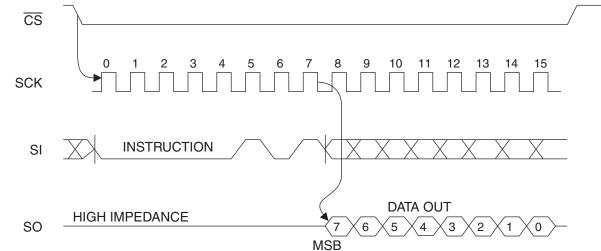


10 AT25320B/640B

AT25320B/640B

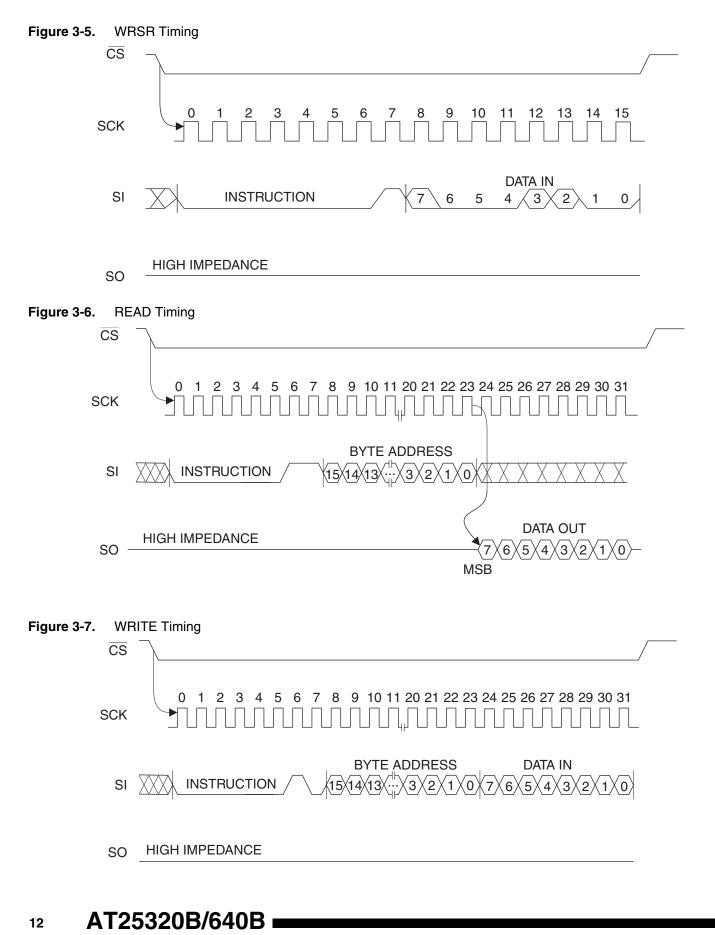






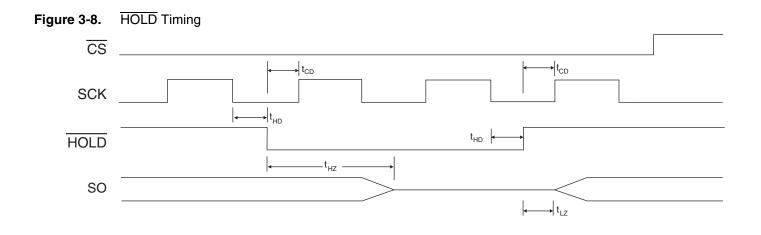






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AT25320B/640B







4. AT25320B Ordering Information

Ordering Code	Voltage	Package	Operation Range
AT25320B-PU (Bulk form only)	1.8	8P3	
AT25320BN-SH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8S1	
AT25320BN-SH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8S1	Lead-free/Halogen-free/ Industrial Temperature (-40 to 85°C)
AT25320B-TH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8A2	
AT25320B-TH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8A2	
AT25320BY6-YH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8Y6	
AT25320BD3-DH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8D3	
AT25320BU2-UU-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8U2-1	
AT25320B-W-11 ⁽³⁾	1.8	Die Sale	Industrial Temperature (-40 to 85°C)

Notes: 1. "B" denotes bulk.

2. "-T" denotes tape and reel. SOIC = 4K per reel. TSSOP, Ultra Thin Mini-MAP, SOT23, and dBGA2 = 5K per reel.

3. Available in waffle pack, tape and reel, and wafer form; order as SL788 for inkless wafer form. Bumped die available upon request. Please contact Serial Interface Marketing.

	Package Type		
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)		
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)		
8A2	8-lead, 4.4 mm Body, Plastic Thin Shrink Small Outline Package (TSSOP)		
8Y6	8-lead, 2.00 mm x 3.00 mm Body, 0.50 mm Pitch, Ultra Thin Mini-MAP, Dual No Lead Package (DFN), (MLP 2x3 mm)		
8D3	8-lead, 1.8 mm x 2.2 mm Body, Ultra Leadframe Land Grid Array (ULA)		
8U2-1	8-lead, 8.35 mm x 3.73 mm Body, 0.75 mm Pitch, VFBGA Package (dBGA2)		
Options			
-1.8	Low Voltage (1.8 to 5.5V)		

5. AT25640B Ordering Information

Ordering Code	Voltage	Package	Operation Range
AT25640B-PU (Bulk form only)	1.8	8P3	
AT25640BN-SH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8S1	
AT25640BN-SH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8S1	
AT25640B-TH-B ⁽¹⁾ (NiPdAu Lead Finish)	1.8	8A2	Lead-free/Halogen-free/
AT25640B-TH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8A2	Industrial Temperature (-40 to 85°C)
AT25640BY6-YH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8Y6	
AT25640BD3-DH-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8D3	
AT25640BU2-UU-T ⁽²⁾ (NiPdAu Lead Finish)	1.8	8U2-1	
AT25640B-W-11 ⁽³⁾	1.8	Die Sale	Industrial Temperature (-40 to 85°C)

Notes: 1. "B" denotes bulk.

2. "-T" denotes tape and reel. SOIC = 4K per reel. TSSOP, Ultra Thin Mini-MAP, SOT23, and dBGA2 = 5K per reel.

3. Available in tape and reel and wafer form; order as SL788 for inkless wafer form. Bumped die available upon request. Please contact Serial Interface Marketing.

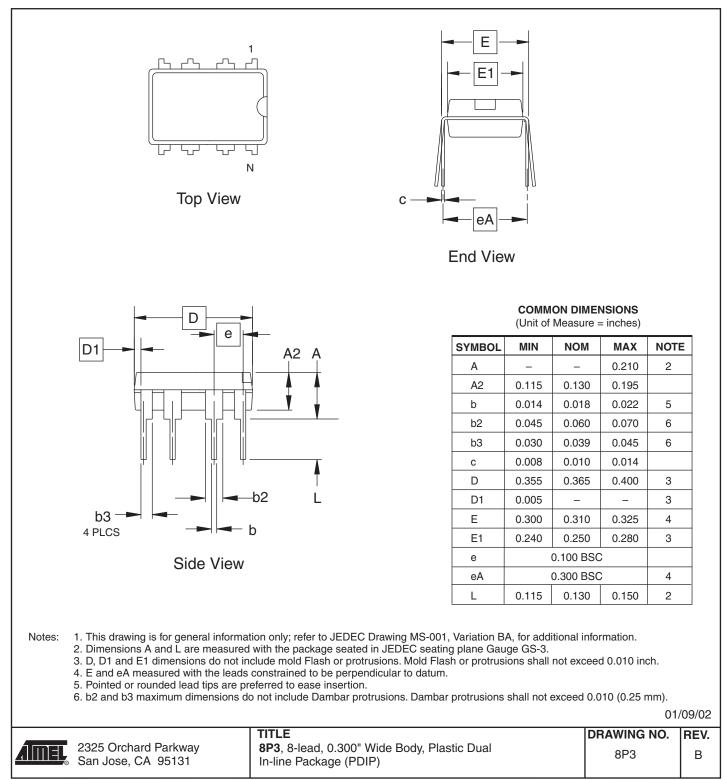
Package Type		
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)	
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)	
8A2	8-lead, 4.4 mm Body, Plastic Thin Shrink Small Outline Package (TSSOP)	
8Y6	8-lead, 2.00 mm x 3.00 mm Body, 0.50 mm Pitch, Ultra Thin Mini-MAP, Dual No Lead Package (DFN), (MLP 2x3mm)	
8D3	8-lead, 1.8 mm x 2.2 mm Body, Ultra Leadframe Land Grid Array (ULA)	
8U2-1	8-lead, 8.35 mm x 3.73 mm Body, 0.75 mm Pitch, VFBGA Package (dBGA2)	
Options		
-1.8	Low Voltage (1.8 to 5.5V)	





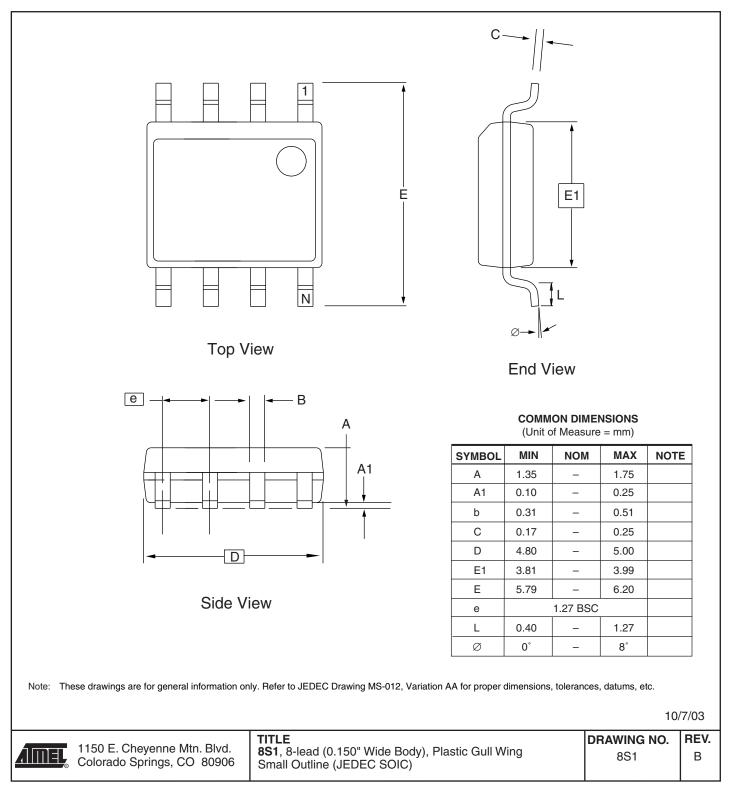
6. Packaging Information

8P3 – PDIP



AT25320B/640B

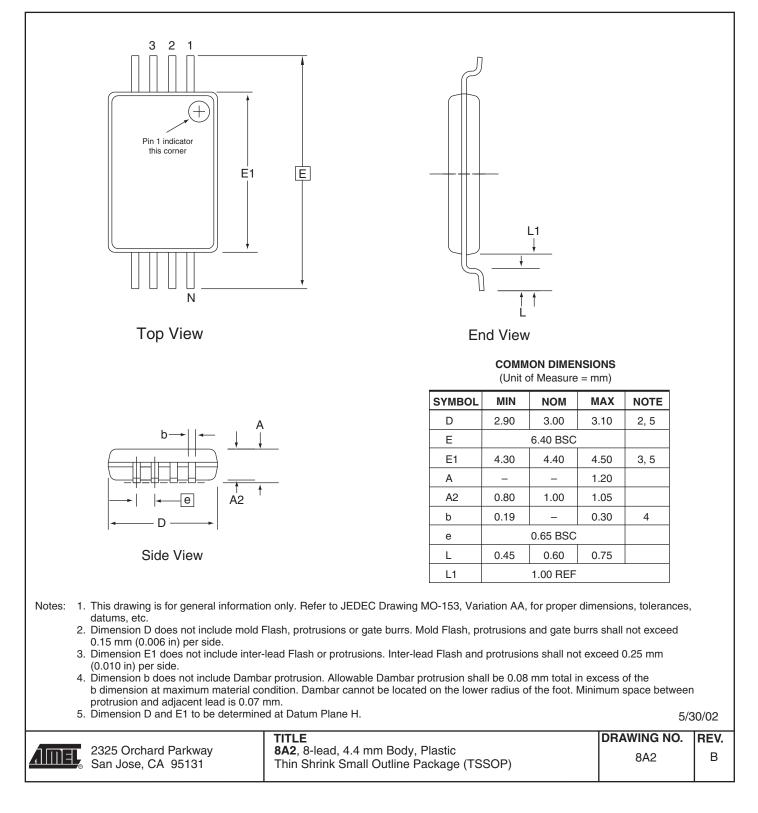
8S1 – JEDEC SOIC



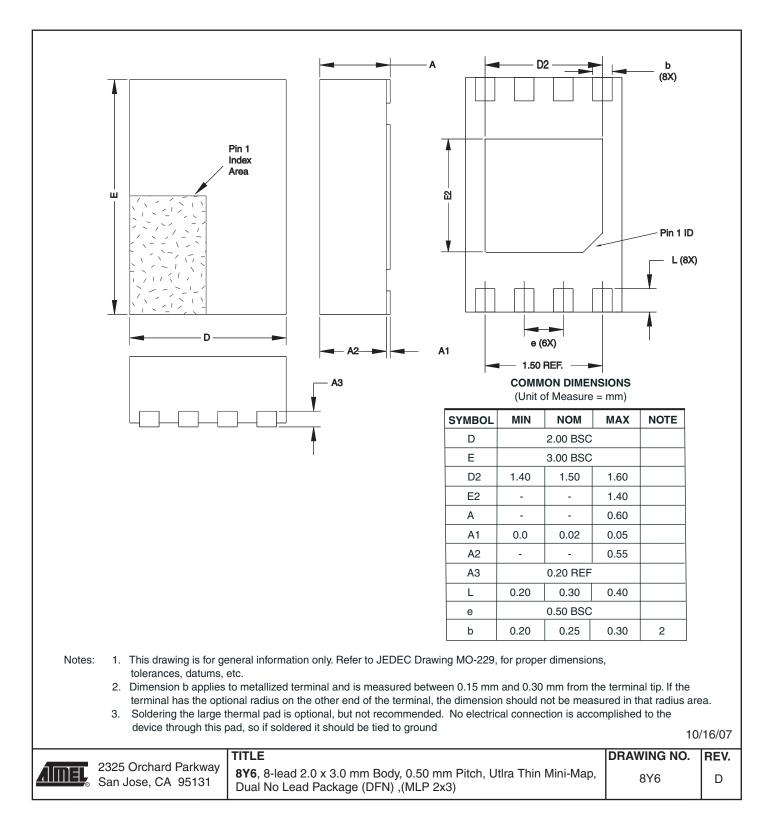




8A2 – TSSOP



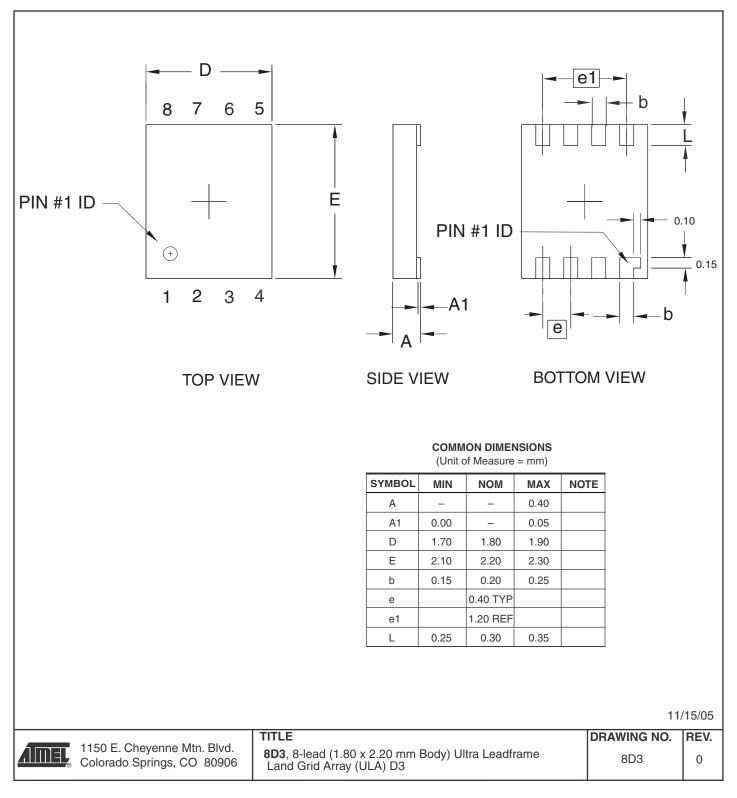
8Y6 – Mini MAP



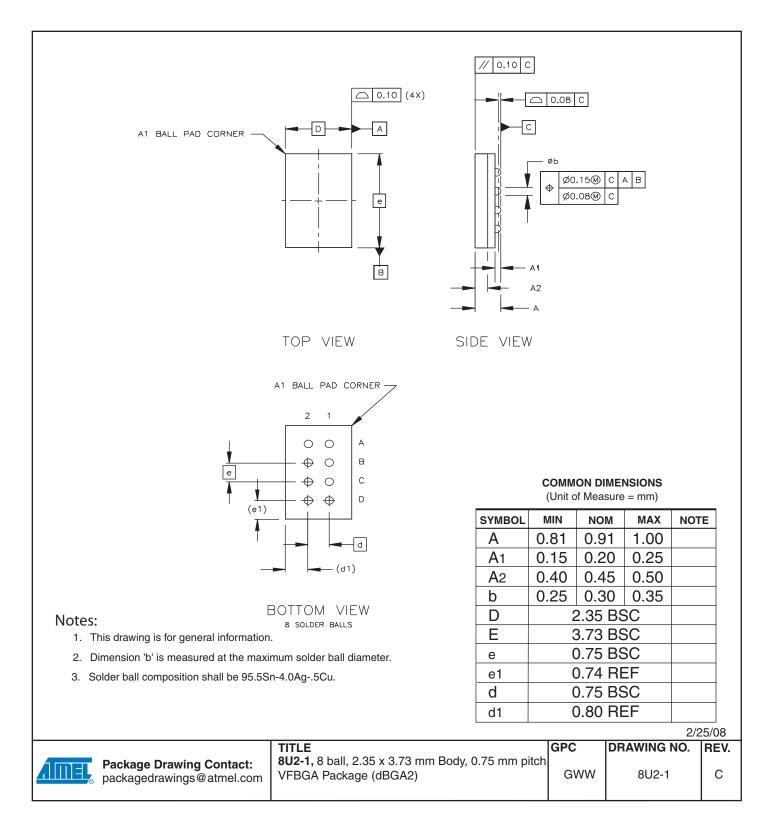




8D3 - ULA



8U2-1 - dBGA2







Revision History

Doc. Rev.	Date	Comments	
8535B	7/2008	Modified 'Endurance' parameter on page 6	
8535A	4/2008	Initial document release.	



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